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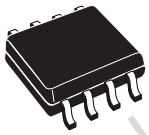
STS4DNF30L

Dual N-channel 30 V, 0.039 Ω, 4 A SO-8 STripFET™ Power MOSFET

Features

Type	V_{DSS}	$R_{DS(on)}$ max.	I_D
STS4DNF30L	30 V	< 0.050 Ω	4 A

- Standard outline for easy automated surface mount assembly
- Low threshold drive



S0-8

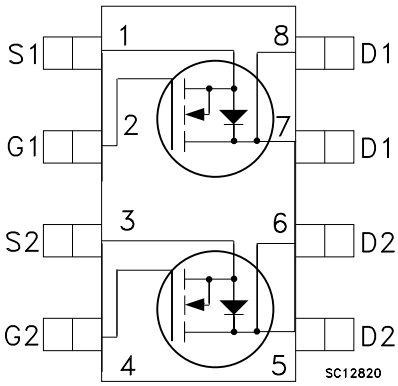
Applications

Switching application

Description

The STS4DNF60L is a dual N-channel STripFET™ Power MOSFET realized with the second generation of STMicroelectronics unique "single feature size" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Figure 1. Internal schematic diagram



Obsolete Product(s) - Obsolete Product(s)

Table 1. Device summary

Order code	Marking	Package	Packaging
STS4DNF30L	4DF30L	SO-8	Tape and reel

Contents

Obsolete Product(s) - Obsolete Product(s)

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (v_{gs} = 0)	30	V
V_{GS}	Gate- source voltage	±16	V
I_D	Drain current (continuos) at T_C = 25°C	4	A
I_D	Drain current (continuos) at T_C = 100°C	2.5	A
I_{DM} (1)	Drain current (pulsed)	16	A
P_{TOT}	Total dissipation at T_C = 25°C dual operating	2	W

1. Pulse width limited by safe operating area

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}a}$ (1)	Thermal resistance junction-ambient max	62.5	°C/W
T_J	Junction temperature	- 55 to 150	°C
T_{stg}	Storage temperature range	150	°C

1. Mounted on FR-4 board (t ≤ 10 sec)

Obsolete Product(s) - Obsolete Product(s)

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	I_D = 250 µA, V_{GS} = 0	30			V
I_{DSS}	Zero gate voltage Drain current (V_{GS} = 0)	V_{DS} = Max rating			1	µA
		V_{DS}= Max rating, T_C = 125 °C			10	µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ± 16 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	1			V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS} = 10 V, I_D = 2 A		0.039	0.050	Ω
		V_{GS} = 4.5 V, I_D = 2 A		0.046	0.060	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 25 V, f = 1 MHz, V_{GS} = 0	-	330		pF
C_{oss}	Output capacitance			90		pF
C_{rss}	Reverse transfer capacitance			40		pF
Q_g	Total gate charge	V_{DD} = 24 V, I_D = 4 A, V_{GS} = 10 V	-	6.5	9	nC
Q_{gs}	Gate-source charge			3.6		nC
Q_{gd}	Gate-drain charge			2		nC

Obsolete Product(s) - Obsolete Product(s)

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	V_{DD} = 15 V, I_D = 2 A, R_G = 4.7 Ω, V_{GS} = 4.5 V (see *Figure 13*)	-	11 100	-	ns ns
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	V_{DD}=15 V, I_D=2 A, R_G=4.7 Ω, V_{GS}= 4.5 V (see *Figure 13*)	-	25 22	-	ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (1)	Source-drain current Source-drain current (pulsed)		-		4 16	A A
V_{SD} (2)	Forward on voltage	I_{SD} = 4 A, V_{GS} = 0	-		1.2	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 4 A, V_{DD} = 20 V di/dt = 100 A/µs, T_j = 150 °C (see *Figure 15*)	-	30 18 1.2		ns nC A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

Obsolete Product(s) - Obsolete Product(s)

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

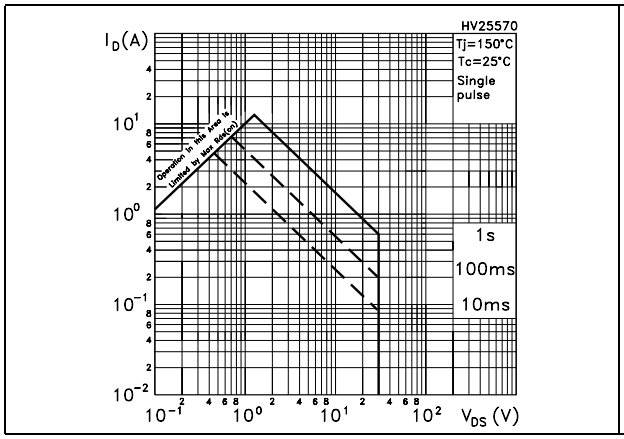


Figure 3. Thermal impedance

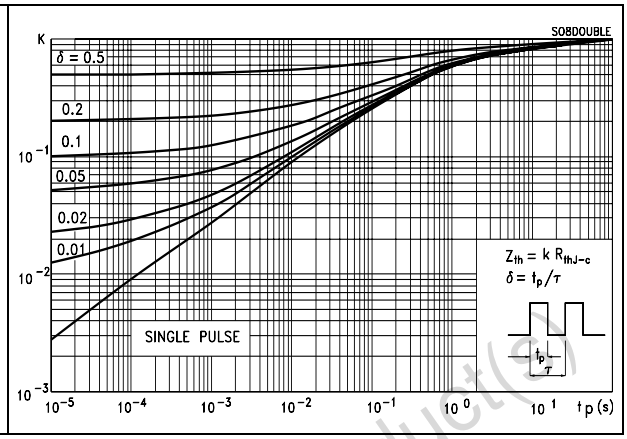


Figure 4. Output characterisics

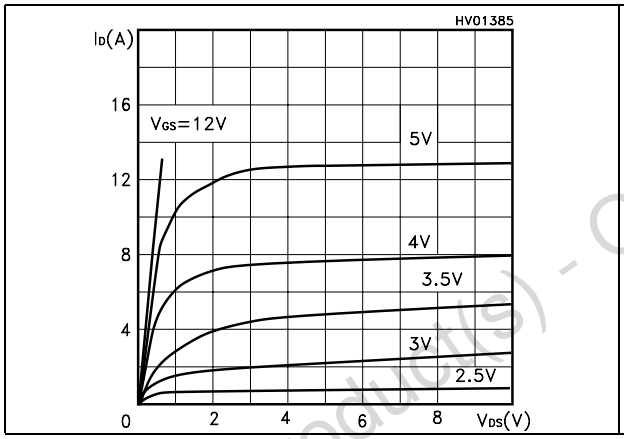


Figure 5. Transfer characteristics

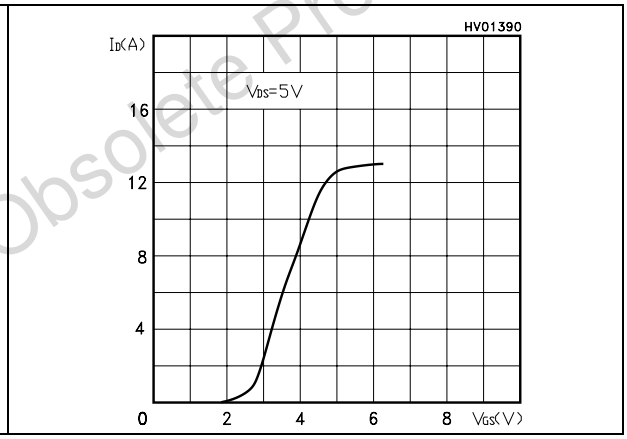


Figure 6. Transconductance

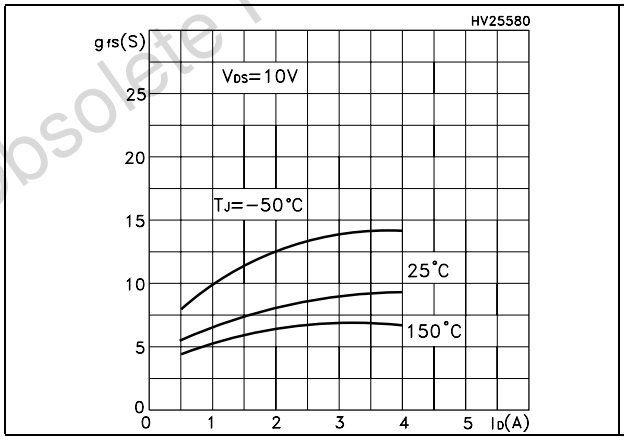
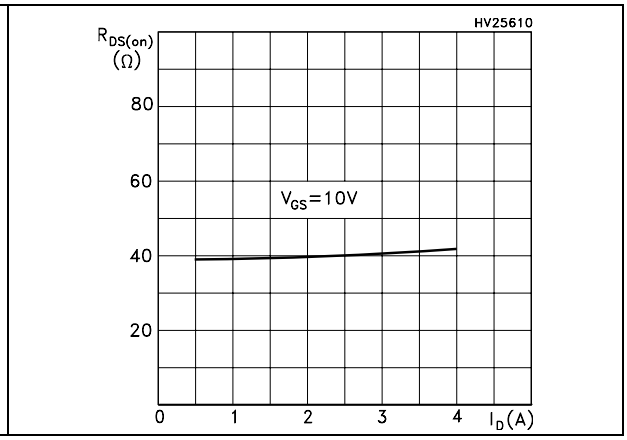


Figure 7. Static drain-source on resistance



Obsolete Product(s) - Obsolete Product(s)

Figure 8. Gate charge vs gate-source voltage

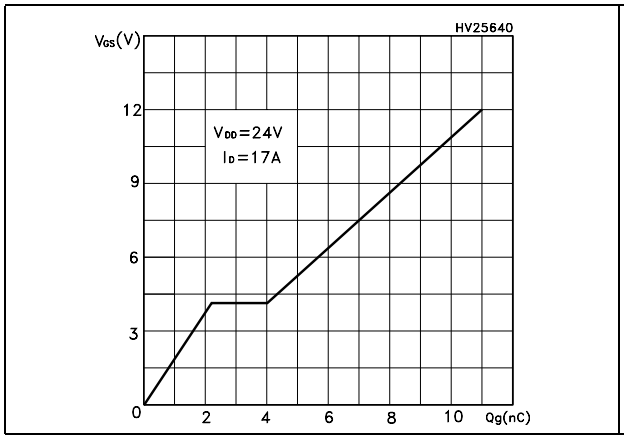


Figure 9. Capacitance variations

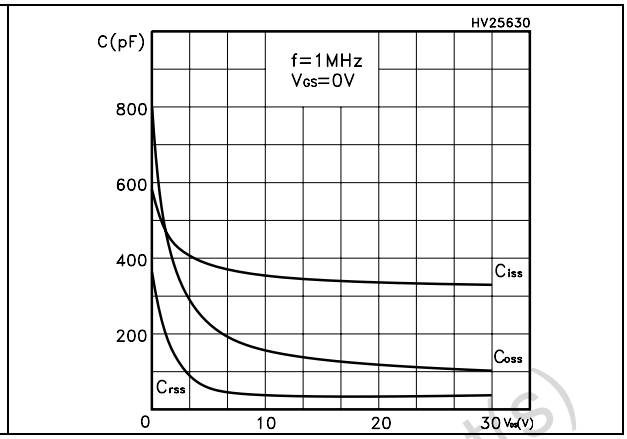


Figure 10. Normalized gate threshold voltage vs temperature

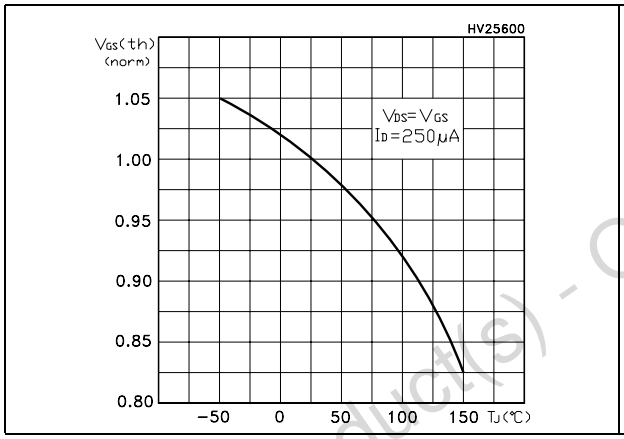


Figure 11. Normalized on resistance vs temperature

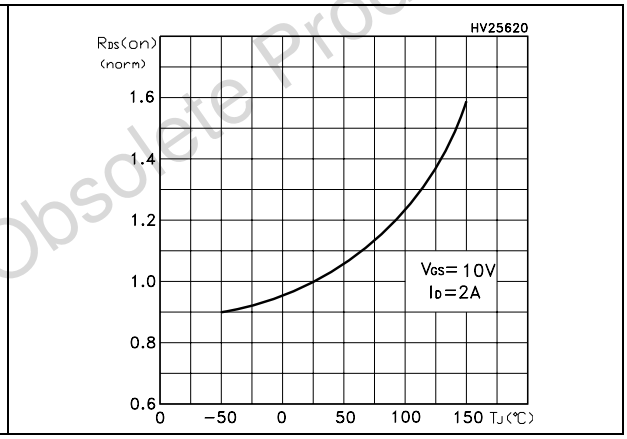
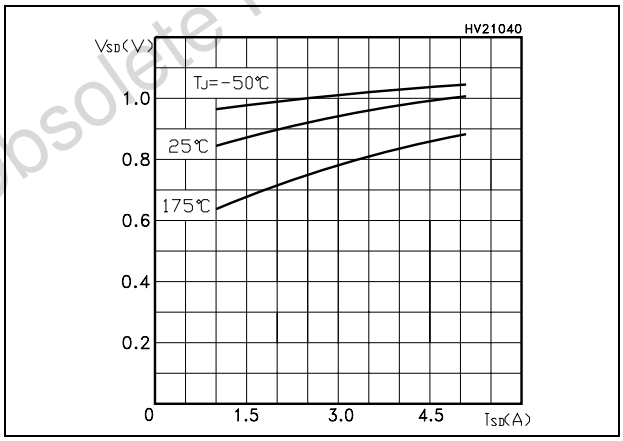


Figure 12. Source-drain diode forward characteristics



Obsolete Product(s) - Obsolete Product(s)

3 Test circuits

Figure 13. Switching times test circuit for resistive load

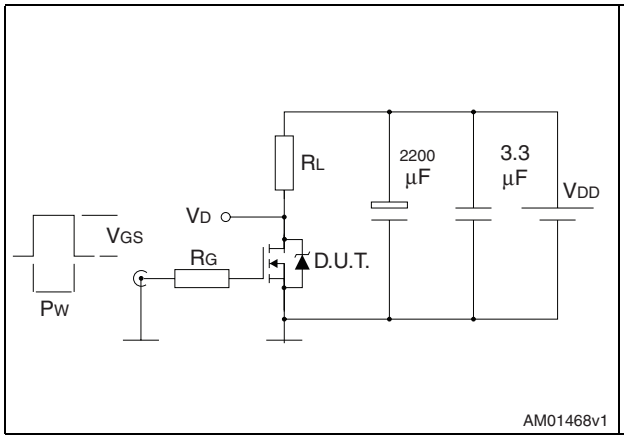


Figure 14. Gate charge test circuit

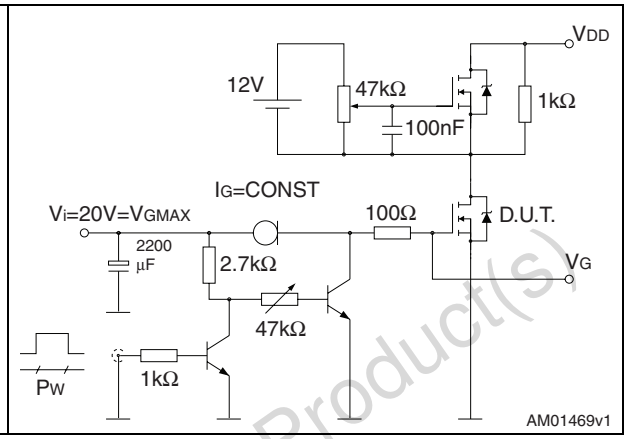


Figure 15. Test circuit for inductive load switching and diode recovery times

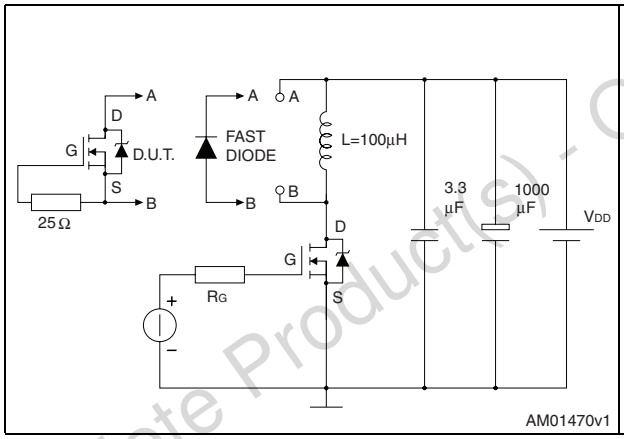


Figure 16. Unclamped Inductive load test circuit

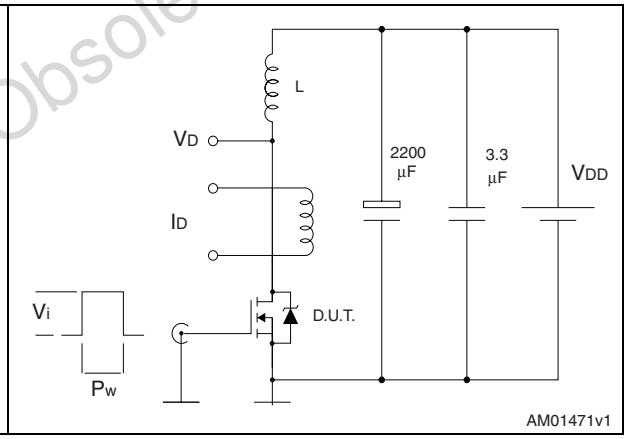


Figure 17. Unclamped inductive waveform

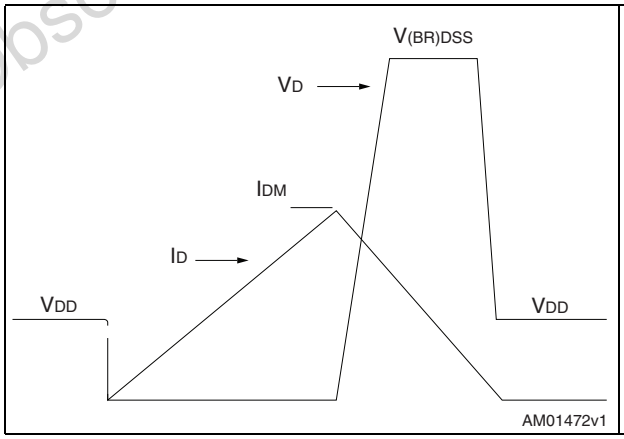
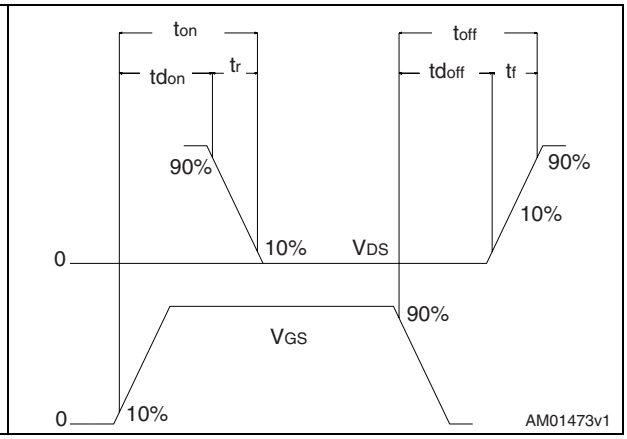


Figure 18. Switching time waveform



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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

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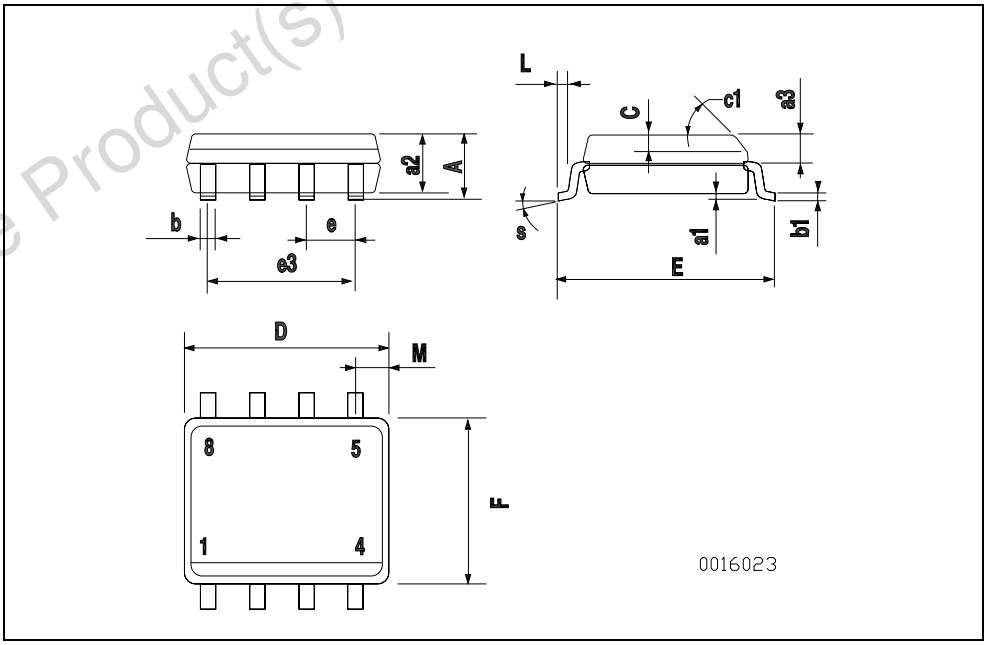
SO-8 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



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5 Revision history

Table 8. Revision history

Date	Revision	Changes
11-Sep-2006	1	First version
15-Nov-2006	2	The document has been reformated
17-Jun-2010	3	Marking in *Table 1: Device summary* has been corrected

Obsolete Product(s) - Obsolete Product(s)

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